MGBR20V100C

DUAL MOS GATED BARRIER RECTIFIER

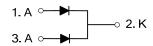
DESCRIPTION

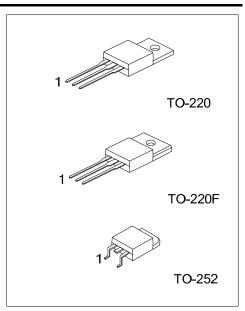
The UTC **MGBR20V100C** is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

■ FEATURES

- * Very low forward voltage drop
- * High switching speed

■ SYMBOL

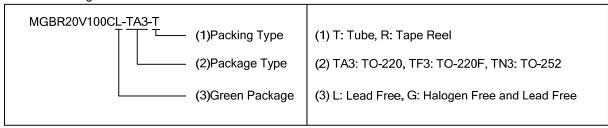




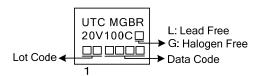
■ ORDERING INFORMATION

Ordering Number		Packago	Pin Assignment			Packing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR20V100CL-TA3-T	MGBR20V100CG-TA3-T	TO-220	Α	K	Α	Tube	
MGBR20V100CL-TF3-T	MGBR20V100CG-TF3-T	TO-220F	Α	K	Α	Tube	
MGBR20V100CL-TN3-R	MGBR20V100CG-TN3-R	TO-252	Α	K	Α	Tape Reel	

Note: Pin Assignment: A: Anode K: Cathode



MARKING



www.unisonic.com.tw 1 of 3

MGBR20V100C DIODE

■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T_A=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		V_{RM}	100	V
Working Peak Reverse Voltage		V_{RWM}	100	V
Peak Repetitive Reverse Voltage		V_{RRM}	100	V
Average Rectified Output Current Per	Per Leg		10	Α
Device	Total	I _O	20	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I _{FSM}	180	Α
Operating Junction Temperature		T_J	-65~+150	°C
Storage Temperature		T_{STG}	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient	TO-220/TO-220F	0	62.5	°C/W	
	TO-252	θ _{JA}	110		
Junction to Case	TO-220		2		
	TO-220F	θ_{JC}	3.31	°C/W	
	TO-252		2.3]	

■ ELECTRICAL CHARACTERISTICS (PER LEG) (T_A =25°C unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I _R =0.50mA	100			V
Forward Voltage Drop	V _{EM}	I _F =10A, T _J =25°C			0.75	٧
		I _F =10A, T _J =125°C			0.70	V
Leakage Current (Note 1)	PМ	V _R =100V, T _J =25°C			100	μA
		V _R =100V, T _J =125°C			10	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

^{2.} Thermal resistance junction to case mounted on heatsink.

MGBR20V100C DIODE

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